

INCHANGE Semiconductor

isc Product Specification

isc Silicon PNP Power Transistor

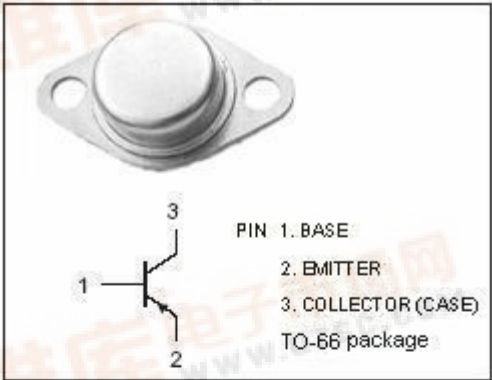
2SA483

DESCRIPTION

- High Collector Current::  $I_C = -1.5A$
- Collector-Emitter Breakdown Voltage  
:  $V_{(BR)CEO} = -150V(\text{Min})$
- Complement to Type 2SC783

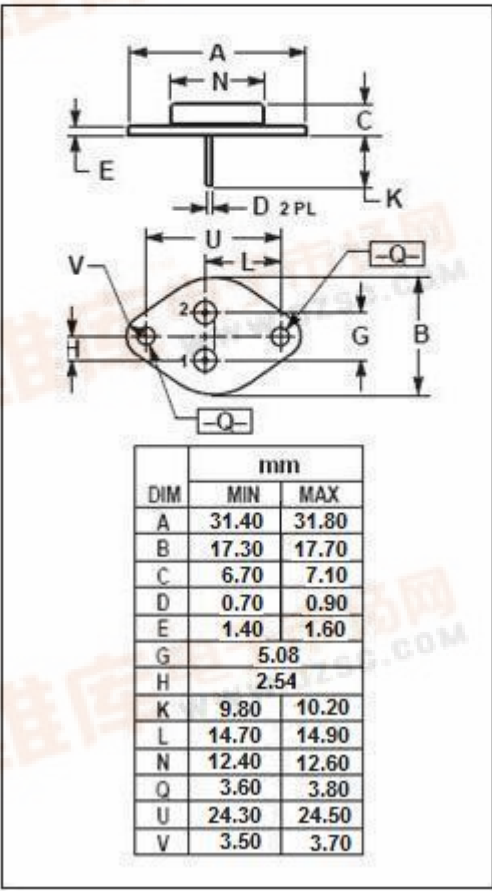
APPLICATIONS

- Power amplifier applications
- Vertical output applications.



ABSOLUTE MAXIMUM RATINGS( $T_a=25^{\circ}C$ )

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	-150	V
$V_{CEO}$	Collector-Emitter Voltage	-150	V
$V_{EBO}$	Emitter-Base Voltage	-5	V
$I_C$	Collector Current-Continuous	-1.5	A
$I_E$	Emitter Current-Continuous	1.5	A
$P_C$	Total Power Dissipation @ $T_C=25^{\circ}C$	20	W
$T_J$	Junction Temperature	150	$^{\circ}C$
$T_{stg}$	Storage Temperature Range	-65~150	$^{\circ}C$



**Silicon PNP Power Transistor****2SA483****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$  unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage	$I_C = -10\text{mA}$ ; $I_B = 0$	-150			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = -0.5\text{mA}$ ; $I_E = 0$	-150			V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = -0.5\text{A}$ ; $I_B = -50\text{mA}$			-1.8	V
$V_{BE(on)}$	Base-Emitter On Voltage	$I_C = -0.5\text{A}$ ; $V_{CE} = -10\text{V}$			-1.8	V
$I_{CBO}$	Collector Cutoff Current	$V_{CB} = -150\text{V}$ ; $I_E = 0$			-100	$\mu\text{A}$
$I_{EBO}$	Emitter Cutoff Current	$V_{EB} = -5\text{V}$ ; $I_C = 0$			-100	$\mu\text{A}$
$h_{FE}$	DC Current Gain	$I_C = -0.1\text{A}$ ; $V_{CE} = -10\text{V}$	30		240	
$f_T$	Current-Gain—Bandwidth Product	$I_C = -0.1\text{A}$ ; $V_{CE} = -10\text{V}$		10		MHz
$C_{OB}$	Output Capacitance	$V_{CB} = -10\text{V}$ ; $f_{test} = 1\text{MHz}$		50		pF

◆  **$h_{FE-1}$  Classifications**

R	O	Y
30-80	70-140	120-240